CURRENT STATUS OF THE CLAIMS

In the Claims

The following is a marked-up version of the claims with the language that is underlined ("___") being added and the language that contains strikethrough ("---") being deleted:

- 1. (Twice Amended) A monolithic waveguide comprising:
 - a <u>planar</u> waveguide core <u>disposed in a fixed position and flush with a lower cladding;</u> an air-gap cladding engaging a portion of the waveguide core; and an overcoat layer engaging a portion of the air-gap cladding and engaging the lower cladding.
- 2. (Previously Amended) The waveguide of claim 1, wherein the waveguide core includes at least one coupling element, wherein the air-gap cladding engages a portion of the at least one coupling element.
- 3. (Original) The waveguide of claim 1, further comprising: at least one coupling element disposed adjacent to the waveguide core.
- 4. (Twice Amended) The waveguide of claim 1, further comprising:

 a second waveguide cladding adjacent to the waveguide core, wherein the air-gap cladding engages a portion of the second waveguide cladding.
- (Twice Amended) The waveguide of claim 1, further comprising:
 a second waveguide core, wherein the air-gap cladding engages a portion of the second waveguide core.

- 6. (Twice Amended) A device, comprising:
 - a monolithic waveguide having a planar waveguide core disposed in a fixed position and flush with a lower cladding, an air-gap cladding engaging a portion of waveguide core, and an overcoat layer engaging a portion of the air-gap cladding, wherein the overcoat layer engages the lower cladding.
 - 7. (Original) The device of claim 6, wherein the waveguide is included in a microelectronic device.
- 8. (Original) The device of claim 6, wherein the waveguide is included in an integrated optical device.
- 9. (Original) The device of claim 6, wherein the waveguide is included in a photonic crystal device.

10-13. (Canceled)

- 14. (Previously Added) The waveguide of claim 1, wherein the overcoat layer is selected from silicon dioxide, silicon nitride, polyimides, polynorbornenes, epoxides, polyarylenes ethers, and parylenes.
- 15. (Previously Added) The waveguide of claim 1, wherein the overcoat layer is selected from polyimides, polynorbornenes, epoxides, polyarylenes ethers, and parylenes.
- 16. (Previously Added) The waveguide of claim 1, wherein the overcoat layer is selected from polyimides and polynorbornenes.
- 17. (Previously Added) The device of claim 6, wherein the overcoat layer is selected from silicon dioxide, silicon nitride, polyimides, polynorbornenes, epoxides, polyarylenes ethers, and parylenes.

- 18. (Previously Added) The device of claim 6, wherein the overcoat layer is selected from polyimides, polynorbornenes, epoxides, polyarylenes ethers, and parylenes.
- 19. (Previously Added) The device of claim 6, wherein the overcoat layer is selected from polyimides and polynorbornenes.

20-27. (Withdrawn)